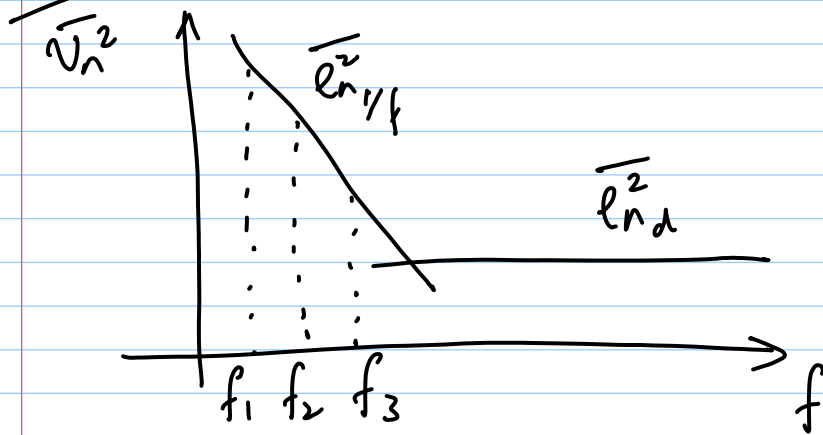


24/1/2012

Note Title

Lec 9

23-01-2012

other forms for $1/f$

noise :

$$\frac{\bar{i}_{n,1/f}^2}{\Delta f} = \frac{k}{f} \frac{g_m^2}{WL C_{ox}}$$

not C_{ox}^2 ...

integrated $1/f$ noise :

$$\bar{i}_{n,1/f}^2 = \frac{k}{f} \frac{g_m^2}{WL C_{ox}^2} \cdot \Delta f$$

$$\Rightarrow \bar{i}_{n,1/f, \text{int}}^2 = \int_{f_1}^{f_2} \bar{i}_{n,1/f}^2 df$$

$$= \frac{k g_m^2}{WL C_{ox}^2} \left[\ln f \right]_{f_1}^{f_2}$$

$$= \frac{k g_m^2}{WL C_{ox}^2} \ln \left(\frac{f_2}{f_1} \right)$$

$\Rightarrow$ total integrated noise is the same in every decade, octave etc.

e.g. $\bar{i}_{n, \text{tot}}^2 (1 \text{ kHz to } 10 \text{ kHz})$

$$= \bar{i}_{n, \text{tot}}^2 (10 \text{ kHz to } 100 \text{ kHz})$$

$1/f$ noise @ very low freq.
(does it go to ∞ ?) :

e.g. Say you are interested in
a signal from 100 Hz to 100 MHz
 $\Rightarrow$ 6 decades

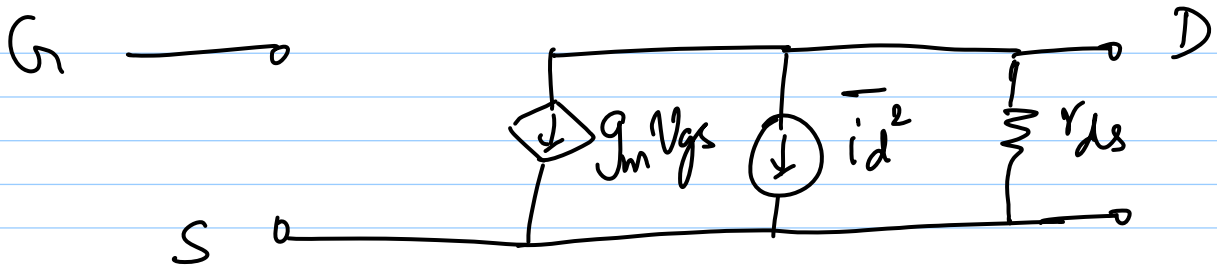
observe signal for 1 day = 86400 s
 $\Rightarrow f_{1\text{-day}} = 1.16 \times 10^{-5}$ Hz

of decades from $f_{1\text{-day}}$ to 100 Hz
 $= 86400 \times 100 \approx 7$

$\therefore$ integration band changes from
6 to 13 decades (if you want
to include noise from $1/\text{day}$ to
100 MHz)

$$\frac{\text{new } \bar{i}_{n,\text{int}}}{\text{old } \bar{i}_{n,\text{int}}} = \sqrt{\frac{13}{6}} = 1.47$$

$\Rightarrow$ only 47% more flicker
noise

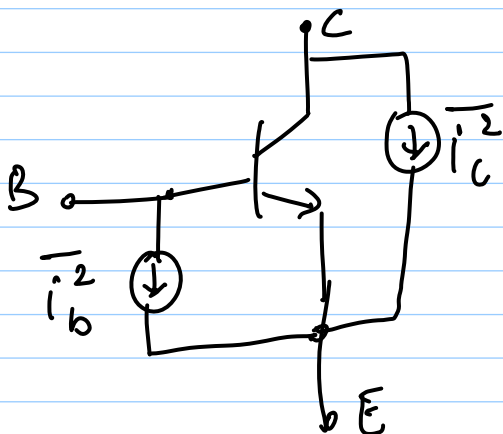


$$\frac{\overline{i_d^2}}{\Delta f} = 4kT \gamma g_m + \frac{k_f}{f} \cdot \frac{g_m^2}{WL C_{ox}^2}$$

* How about noise of r_{ds} ?

→ r_{ds} is noiseless – only a virtual resistor that models $\partial I_D / \partial V_{DS}$ due to CLM

Bipolar Transistor noise:



2 shot noise sources (uncorrelated)

$$\overline{i_c^2} = 2q I_C \Delta f = 2kT g_m \Delta f$$

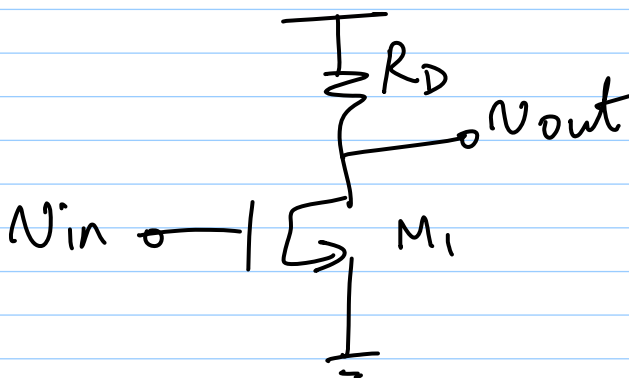
$$\begin{aligned} \overline{i_b^2} &= 2q I_B \Delta f = 2kT \cdot \frac{g_m}{\beta} \Delta f \\ &= \frac{2kT}{r_{\pi}} \Delta f \end{aligned}$$

BJT flicker noise

$$\overline{i_b^2} \approx \frac{K_1 I_B^a}{f} \quad \text{usually small enough to be negligible}$$

$1/f$ noise of BJT is much smaller than that of MOSFETs

E.g. CS stage



$$\frac{\overline{V_{n,out}^2}}{\Delta f} = \left\{ 4kT \gamma g_m + \frac{K}{f} \frac{g_m^2}{W L C_{ox}^2} + \frac{4kT}{R_D} \right\} R_D^2$$

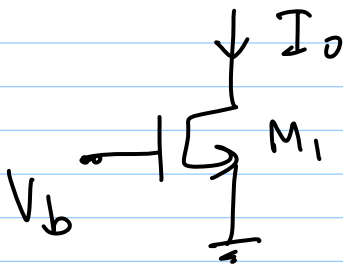
$$a_v = -g_m R_D$$

$$\therefore \frac{\overline{v_{n,in}^2}}{\Delta f} = \frac{1}{(a_v)^2} \cdot \overline{v_{n,out}^2}$$

$$= \frac{4KT \gamma}{g_m} + \frac{k}{f} \cdot \frac{1}{WL C_{ox}^2} + \frac{4KT}{g_m^2 R_D}$$

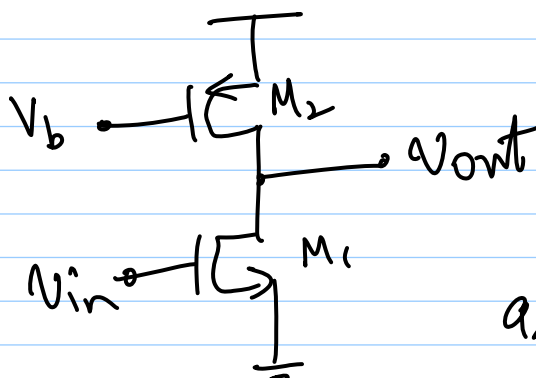
$\Rightarrow$ maximise g_m to minimise $\overline{v_{n,in}^2}/\Delta f$

large $g_m \Rightarrow$ lower input-referred voltage noise



* When operated as a current source - minimise g_m !

e.g.



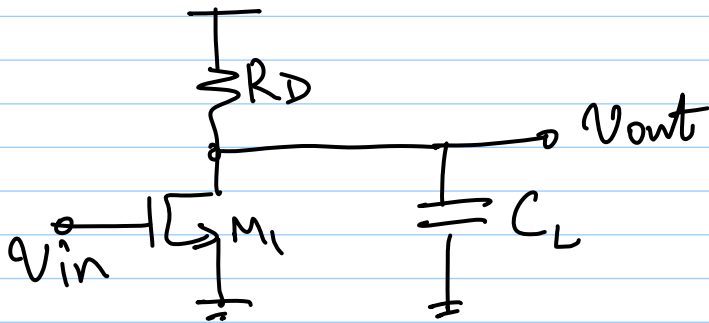
$$\frac{\overline{v_{n,out}^2}}{\Delta f} = 4KT(\gamma_1 g_{m1} + \gamma_2 g_{m2}) \cdot (r_{ds1} || r_{ds2})^2$$

$$a_v = -g_{m1} \cdot (r_{ds1} || r_{ds2})$$

$$\Rightarrow \frac{\overline{v_{n,in}^2}}{\Delta f} = 4KT \left[\frac{\gamma_1}{g_{m1}} + \frac{\gamma_2 g_{m2}}{g_{m1}^2} \right]$$

⇒ maximise g_{m1} & minimise g_{m2}

load cap:



$$\frac{\overline{v_{n,out}^2}}{\Delta f} = \left[4kT \gamma g_m + \frac{k}{f} \cdot \frac{g_m^2}{WL C_{ox}^2} + \frac{4kT}{R_D} \right] \cdot \left| R_D \parallel \frac{1}{j\omega C_L} \right|^2$$

$$= \left[4kT \gamma g_m + \frac{k}{f} \frac{g_m^2}{WL C_{ox}^2} + \frac{4kT}{R_D} \right] R_D^2 \cdot \frac{1}{1 + (\omega R_D C_L)^2}$$

⇒ o/p PSD shaped by squared magnitude of 1-pole response

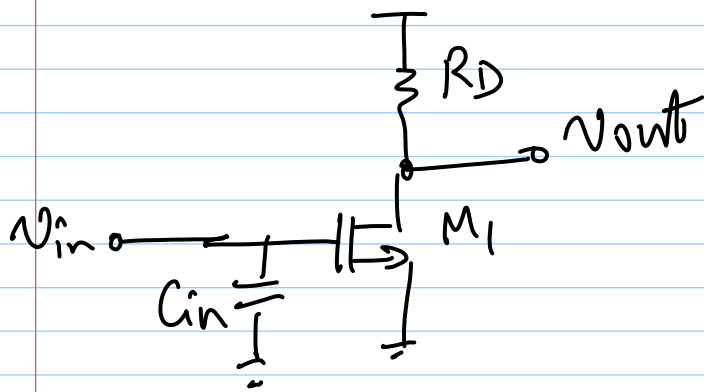
$$a_v(j\omega) = -g_m \cdot \left(R_D \parallel \frac{1}{j\omega C_L} \right)$$

$$|a_v(j\omega)|^2 = g_m^2 R_D^2 / [1 + (\omega R_D C_L)^2]$$

$$\frac{\overline{v_{n,in}^2}}{\Delta f} = \frac{4kT \gamma}{g_m} + \frac{k}{f} \cdot \frac{1}{WL C_{ox}^2} + \frac{4kT}{g_m^2 R_D}$$

⇒ input-referred noise is same as before because $\bar{v}_{n,out}$ and gain have same freq. roll-off (all noise is being added before RC-pole)

Input Cap



$$\overline{v_{n,in}^2} = ?$$

$$\overline{i_{n,in}^2} = ?$$

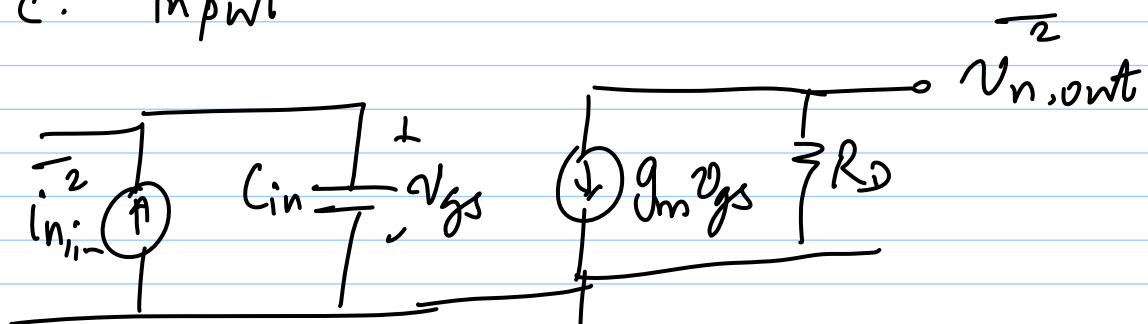
neglect $1/f$ noise

$$\overline{v_{n,in}^2} = \text{same as before}$$

Δf (C_{in} falls in shunt across CS)

But now, an $\overline{i_{n,in}^2}$ exists:

O.C. input



$$v_{gs}^2 = \overline{i_{n,in}^2} \cdot |1/j\omega C_{in}|^2$$

$$\overline{v_{n,out}^2} = g_m^2 \cdot \overline{i_{n,in}^2} \cdot \frac{1}{(wC_{in})^2} \cdot R_D^2$$

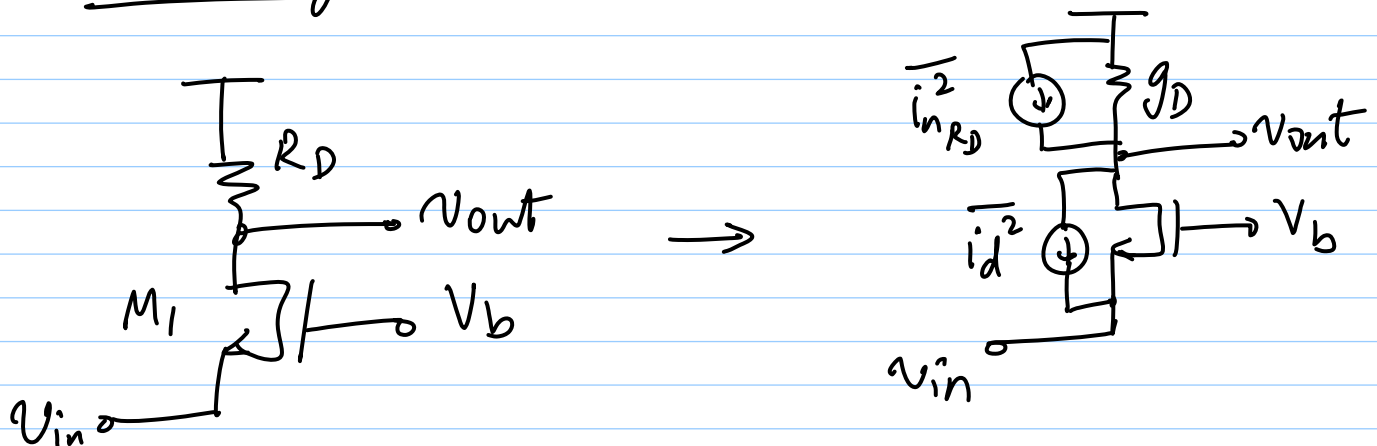
actual $\overline{v_{n,out}^2} = \left(4kT \gamma g_m + \frac{4kT}{R_D} \right) R_D^2 \cdot \Delta f$
 Equate the two:

$$\frac{\overline{i_{n,in}^2}}{\Delta f} = \left(\frac{4kT \gamma}{g_m} + \frac{4kT}{g_m^2 R_D} \right) (wC_{in})^2$$

$$= \frac{4kT}{g_m^2} (wC_{in})^2 \left[\gamma g_m + \frac{1}{R_D} \right]$$

① low freq., $\overline{i_{n,in}^2}$ is insignificant

CA stage

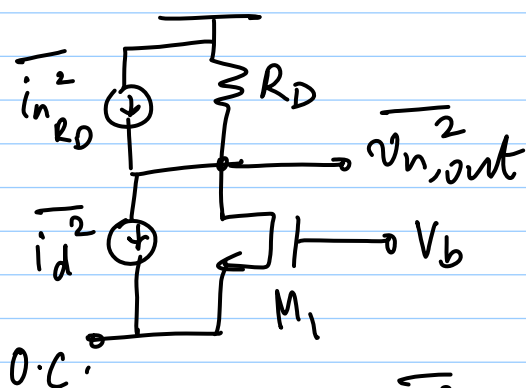


* input impedance is low $\Rightarrow \overline{i_n^2}$ is significant even @ low freq.

$$(4kT \gamma g_m + 4kT g_D) R_D^2 \Delta f = \overline{v_{n,in}^2} (g_m + g_{mbs})^2 R_D^2$$

$$\frac{\overline{v_{n, in}^2}}{\Delta f} = \frac{4kT (\gamma g_m + g_D)}{(g_m + g_{mbs})^2}$$

O.C. input :



* i_d^2 flows completely through M_1
 $\Rightarrow$ produces no noise @ output

$$\frac{\overline{v_{n, out}^2}}{\Delta f} = 4kT g_D \cdot R_D^2 = 4kT R_D$$

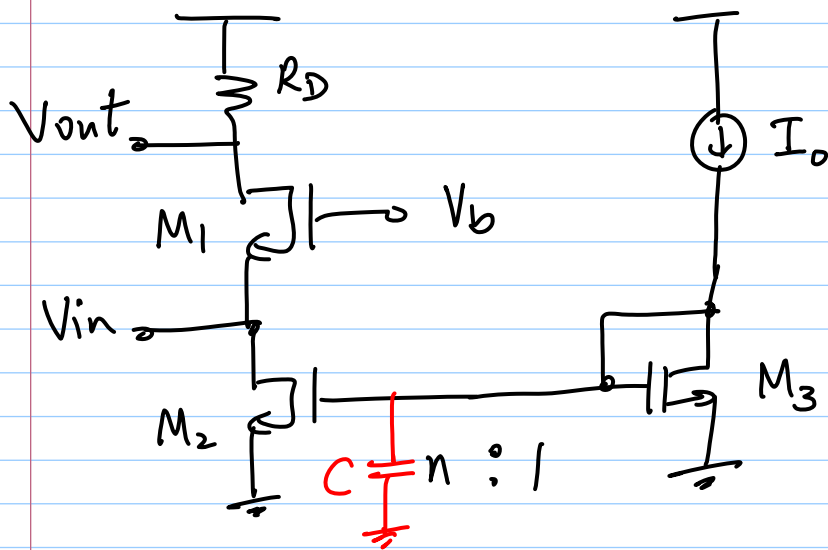
With input-referred source:

$$\overline{v_{n, out}^2} = \overline{i_{n, in}^2} \cdot R_D^2$$

$$\Rightarrow \frac{\overline{i_{n, in}^2}}{\Delta f} = \frac{4kT}{R_D}$$

* C.G. stage directly refers load noise current to the input
 $\Rightarrow$ C.G. has no current gain.

C.C. w/ bias



* noise of M_0
 — gets multiplied
 into signal path
 $\Rightarrow$ add cap C
 to shunt this
 noise to gnd

* Noise of M_2 :
 S.C. input $\Rightarrow \overline{i_{d2}^2}$ flows into S.C.

$\Rightarrow \overline{v_{n, \text{in}}^2}$ is same as before

O.C. input:

all of $\overline{i_{d2}^2}$ flows into R_D to produce

$$\overline{v_{n, \text{out}, M_2}^2} = \overline{i_{d2}^2} \cdot R_D^2$$

$\Rightarrow \overline{i_{d2}^2}$ directly adds to $\overline{i_{n, \text{in}}^2}$

* minimise g_{m2}

$\Rightarrow$ for given bias current, V_{DSAT2} increases

$\Rightarrow V_{b2} \uparrow \Rightarrow$ output voltage swing $\downarrow$